



(12) **Patent Application Publication**  
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(43) **Pub. Date:** **Jul. 20, 2023**

(2006.01)

(2006.01)

(52) U.S. Cl.

CPC .. ***H01L 21/823821*** (2013.01); ***H01L 27/0924***  
(2013.01); ***H01L 21/0337*** (2013.01); ***H01L***  
***21/31144*** (2013.01); ***H01L 21/823871***  
(2013.01)

(57)

## ABSTRACT

An embodiment method includes: forming fins extending from a semiconductor substrate; depositing an inter-layer dielectric (ILD) layer on the fins; forming masking layers on the ILD layer; forming a cut mask on the masking layers, the cut mask including a first dielectric material, the cut mask having first openings exposing the masking layers, each of the first openings surrounded on all sides by the first dielectric material; forming a line mask on the cut mask and in the first openings, the line mask having slot openings, the slot openings exposing portions of the cut mask and portions of the masking layers, the slot openings being strips extending perpendicular to the fins; patterning the masking layers by etching the portions of the masking layers exposed by the first openings and the slot openings; and etching contact openings in the ILD layer using the patterned masking layers as an etching mask.

(22) Filed: **Mar. 24, 2023**

### Related U.S. Application Data

(63) Continuation of application No. 17/705,943, filed on Mar. 28, 2022, now Pat. No. 11,615,991, which is a continuation of application No. 16/884,972, filed on May 27, 2020, now Pat. No. 11,289,383.

## Publication Classification

(51) **Int. Cl.**  
*H01L 21/8238* (2006.01)  
*H01L 27/092* (2006.01)

